

Application No.: 10/017,805

Docket No.: JCLA7245

In The Claims:

1. (Currently Amended) A photoresist ~~with an adjustable~~ to a polarized light response ~~suitable~~ for use in a photolithography process, the photoresist comprising:

a photosensitive polymer, wherein: ~~the photosensitive polymer absorbs an exposure light source to generate an optical reaction in the photolithography process;~~ the photosensitive polymer is oriented to a specific direction ~~by a physical method;~~ and under an electromagnetic field, and the photosensitive polymer comprises a photosensitive section for absorbing an exposure light to generate an optical reaction and an anti-etching section for increasing a resist force against a plasma etching, and the photosensitive polymer is able ~~has a~~ response to a polarized light, ~~wherein the response varies as~~ according to an angle variation between the specific direction and a polarization direction of the polarized light changes.

2. (Original) The photoresist according to claim 1, wherein the linear photosensitive polymer includes a linear photosensitive polymer.

3. (Original) The photoresist according to claim 2, wherein when a direction of the linear photosensitive polymer is parallel to the polarization direction of the polarized light, the liner photosensitive polymer has a maximum polarized light response, and when the direction of the linear photosensitive polymer is perpendicular to the polarization direction of the polarized light, the liner photosensitive polymer has a minimum polarized light response.

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Claim 4. (canceled)

5. (Currently Amended) The photoresist according to claim 14, wherein the photosensitive section includes a PMDA.

6. (Currently Amended) The photoresist according to claim 14, wherein the photosensitive section has a molecule weight of $10^2 \sim 10^8$.

7. (Currently Amended) The photoresist according to claim 14, wherein the anti-etching section includes ODA.

8. (Currently Amended) The photoresist according to claim 14, wherein the photosensitive section has a molecule weight as $10^2 \sim 10^8$.

9. (Currently Amended) The photoresist according to claim 1, wherein the physical method electromagnetic field is ~~includes applying~~ an electric field and ~~when~~ the photosensitive polymer has electric dipoles.

10. (Currently Amended) The photoresist according to claim 9, wherein applying the an electric field includes using a plasma.

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11. (Currently Amended) The photoresist according to claim 9, wherein applying the an electric field includes using a polarized ultra-violet light.

12. (Currently Amended) The photoresist according to claim 9, wherein applying the an electric field includes using a microwave.

13. (Currently Amended) The photoresist according to claim 1, wherein the ~~physial method-electromagnetic field is~~ includes applying a magnetic field and when the photosensitive polymer has magnetic dipoles.

14. (Currently Amended) The photoresist according to claim 139, wherein applying the a magnetic field includes using a plasma.